

M54561P

7-UNIT 300mA SOURCE TYPE DARLINGTON TRANSISTOR ARRAY WITH CLAMP DIODE

DESCRIPTION

M54561P is seven-circuit output-sourcing Darlington transistor arrays. The circuits are made of PNP and NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

FEATURES

- High breakdown voltage ($BV_{CEO} \geq 40V$)
- High-current driving ($I_o(max) = -300mA$)
- With output clamping diodes
- Active "L" input
- Wide operating temperature range ($T_a = -20$ to $+75^\circ C$)

APPLICATION

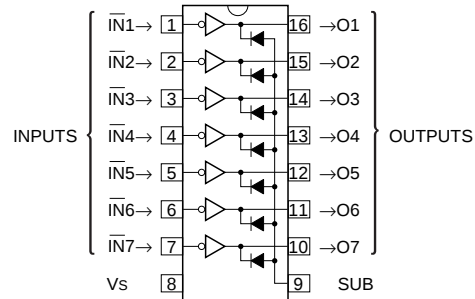
Drives of relays, printers, LEDs, fluorescent display tubes and lamps, and interfaces between MOS-bipolar logic systems and relays, solenoids, or small motors

FUNCTION

The M54561P have seven circuits of current-sourcing outputs. Darlington transistor, which are made of PNP transistor and NPN transistor. Resistance of $20k\Omega$ is connected between PNP transistor base and input pin. PNP transistor emitters and NPN transistor collector is connected V_s (pin 8), and spike killer clamping diode is provided between each output pins.

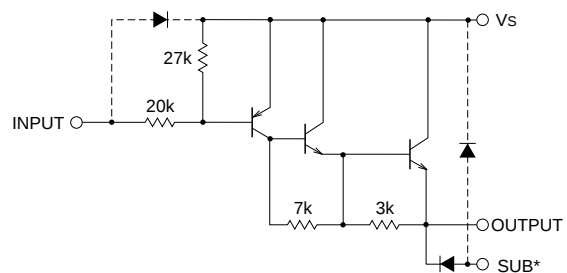
Output current is 300mA maximum and supply voltage V_s is 40V maximum operate Active "L" input.

PIN CONFIGURATION (TOP VIEW)



Outline 16P4

CIRCUIT SCHEMATIC



* SUB must be the lowest voltage in a circuit.

The seven circuits share the V_s and SUB.

The diodes shown by broken line are parasite diodes and must not be used.

Unit : Ω

ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, $T_a = -20 \sim +75^\circ C$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CEO}	Collector-emitter voltage	Output, L	$-0.5 \sim V_s$	V
V_s	Supply voltage		40	V
V_i	Input voltage		$-0.5 \sim V_s$	V
I_o	Output current	Current per circuit output, H	-300	mA
I_F	Clamping diode forward current		-300	mA
V_R	Clamping diode reverse voltage		40	V
P_d	Power dissipation	$T_a = 25^\circ C$, when mounted on board	1.47	W
T_{opr}	Operating temperature		$-20 \sim +75$	$^\circ C$
T_{stg}	Storage temperature		$-55 \sim +125$	$^\circ C$

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RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, $T_a = -20 \sim +75^\circ\text{C}$)

Symbol	Parameter	Limits			Unit
		min	typ	max	
V_s	Supply voltage	0	—	40	V
I_o	Output current per channel	0	—	-300	mA
		0	—	-100	
V_{IH}	"H" input voltage	$V_s - 0.2$	—	$V_s + 0.3$	V
V_{IL}	"L" input voltage	0	—	$V_s - 3$	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, $T_a = -20 \sim +75^\circ\text{C}$)

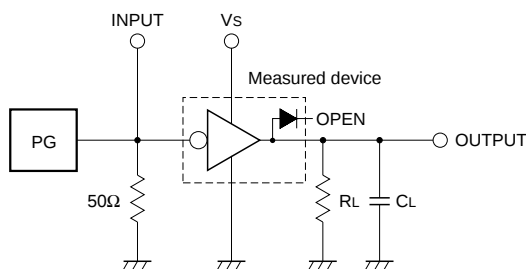
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ*	max	
I_s (leak)	Supply leak current	$V_s = 40\text{V}$	—	—	100	μA
V_{CE} (sat)	Collector-emitter saturation voltage	$V_i = V_s - 3\text{V}$, $I_o = -300\text{mA}$	—	1.65	2.4	V
		$V_i = V_s - 3\text{V}$, $I_o = -100\text{mA}$	—	1.45	2.0	
I_i	Input current	$V_i = V_s - 3.5\text{V}$,	—	-150	-250	μA
V_F	Clamping diode forward voltage	$I_F = -300\text{mA}$	—	-1.6	-2.4	V
I_R	Clamping diode reverse current	$V_R = 40\text{V}$	—	—	100	μA
h_{FE}	DC amplification factor	$V_{CE} = 4\text{V}$, $I_o = -300\text{mA}$, $T_a = 25^\circ\text{C}$	1000	8000	—	—

* : The typical values are those measured under ambient temperature (T_a) of 25°C . There is no guarantee that these values are obtained under any conditions.

SWITCHING CHARACTERISTICS (Unless otherwise noted, $T_a = 25^\circ\text{C}$)

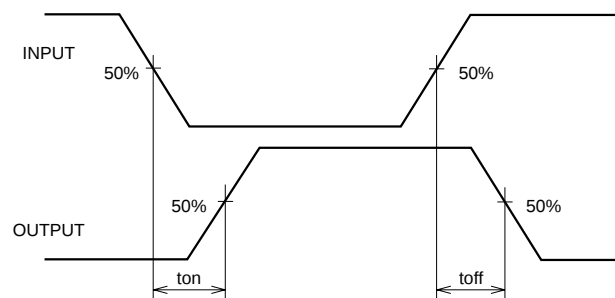
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
t_{on}	Turn-on time	$C_L = 15\text{pF}$ (note 1)	—	200	—	ns
t_{off}	Turn-off time		—	2500	—	ns

NOTE 1 TEST CIRCUIT



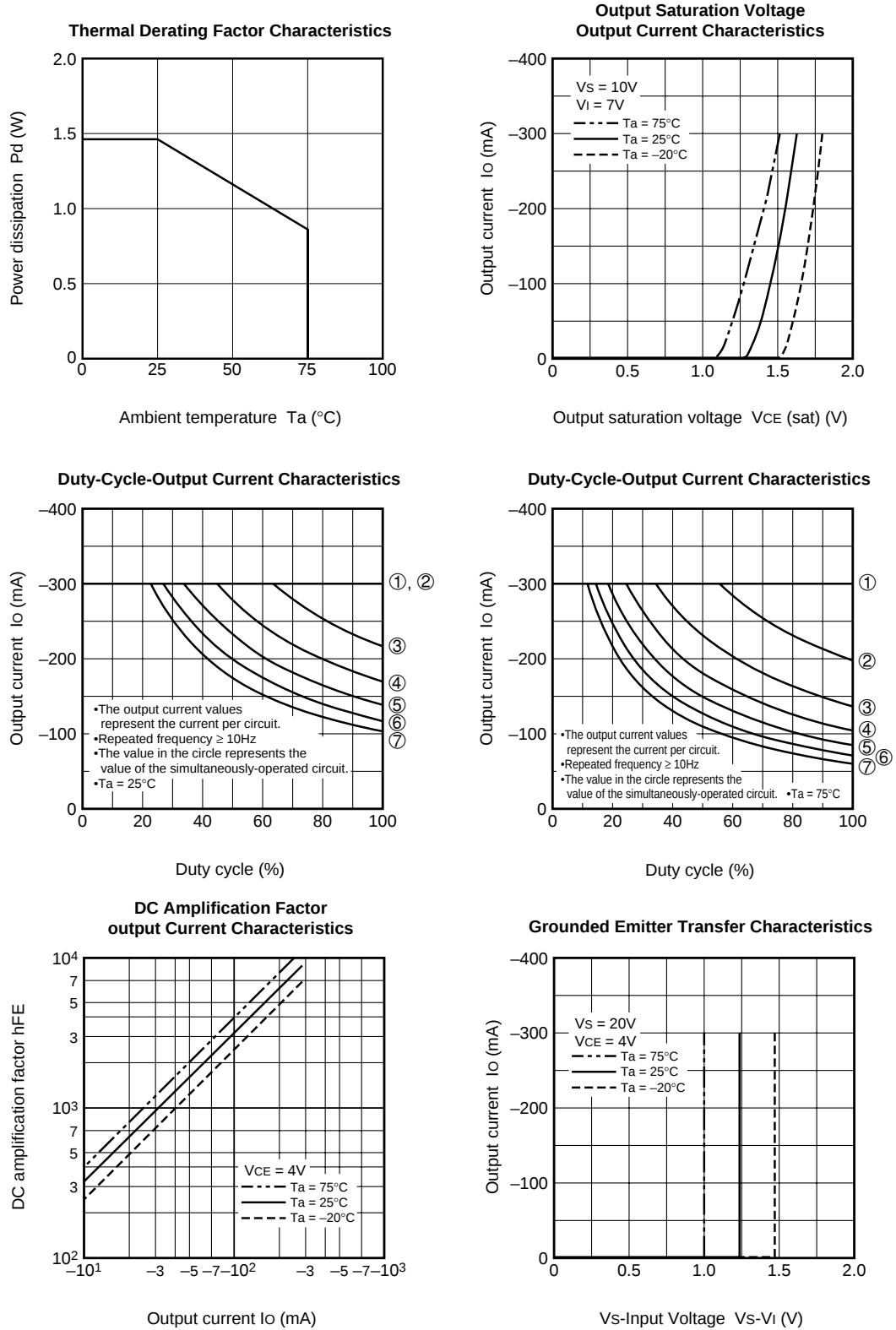
- (1) Pulse generator (PG) characteristics : PRR = 1kHz,
 $t_w = 10\mu\text{s}$, $t_r = 6\text{ns}$, $t_f = 6\text{ns}$, $Z_o = 50\Omega$
 $V_{IN} = 7$ to 10.3V
- (2) Input-output conditions : $R_L = 40\Omega$, $V_s = 10\text{V}$
- (3) Electrostatic capacity C_L includes floating capacitance at connections and input capacitance at probes

TIMING DIAGRAM



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TYPICAL CHARACTERISTICS



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